

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A set of at least two masks for the projection of structure patterns, each structure pattern being formed on the masks and coordinated with one another by a projection system into the same photosensitive layer arranged on a semiconductor wafer, the projection system having a resolution limit for a lateral dimension of an opening projected onto the semiconductor wafer from a mask, comprising:

a first mask, ~~the first mask having~~ including a semitransparent or nontransparent first layer, which is arranged on a first substrate and in which at least one first opening is formed at a first position, the first opening having a first lateral dimension, which is greater than the resolution limit; and

a second mask assigned to the first mask, the second mask ~~having~~ including a semitransparent or nontransparent second layer, which is arranged on a second substrate and in which at least one dummy structure assigned to the first opening is formed at a second position, the dummy structure having a second lateral dimension, which is smaller than the resolution limit of the projection system wherein the first position on the first mask is identical to the second position on the second mask.

2. (Currently Amended) The set of masks as claimed in claim 1, wherein one of the first and second masks is a chromeless or alternating phase mask.

3. (Currently Amended) The set of masks as claimed in claim 2, wherein the ~~second~~ other of the first and second masks is a trimming mask having at least one further opening for the exposure of a region in the photosensitive layer, which arises on account of a phase conflict in the case of an exposure with ~~the first~~ said one of the first and second masks.

4. (Canceled)

5. (Original) The set of masks as claimed in claim 1, wherein the first opening, a second opening, and at least one third opening are arranged as gaps in a periodic line-gap pattern on the first mask.

6. (Original) The set of masks as claimed in claim 5, wherein the first, second, and at least third opening, as gaps, are separated from one another by first, second and third webs formed by the semitransparent or nontransparent first layer, the first, second, and at least third opening case have the same first lateral dimension, the first, second and third web each case have an identical third lateral dimension, and the first and the third lateral dimension are different from one another.

7. (Original) The set of masks as claimed in claim 6, wherein the first, second, and at least third opening are in each case assigned a dummy structure, the position of the first, second and at least third opening on the first mask each being identical to that position of the dummy structure assigned thereto on the second mask.

8. (Original) The set of masks as claimed in claim 1, wherein at least one further transparent opening is formed at a further first position on the first mask, and at least one semitransparent region is arranged at a further second position on the second mask, the further second position corresponding to the further first position on the first mask.

9-15. (Canceled)